



# Material technology enhances the density and the productivity of the package

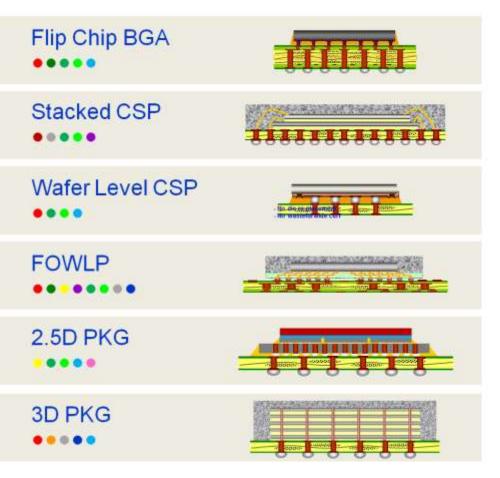
May 31, 2018

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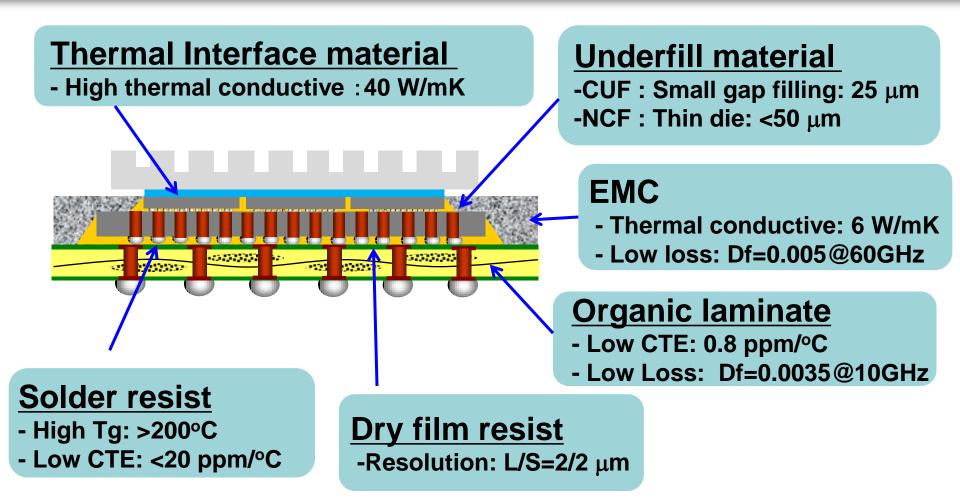
# Outline

Materials for high density packaging
 Bonding Force Leveling (BFL) Film
 Molded reflow process with NCF & EMC
 Bump Stabbing process
 RDL-first FO-PLP TV and "JOINT"
 Summary



- Buffer Coatings/Redistribution Materials
- CMP Slurry
- Die Attach Film
- Dielectric Material/Build UP, SAP Prepreg
- Dry Film Resist
- Release Film
- Substrate
- Solder Resist
- Temporary Bonding Film
- Solid/Liquid EMC, Embedded Sheet
- Thermally Conductive Film
- Temporary Bonding Film
- Underfill

### Material can contribute to the performance of the high density package

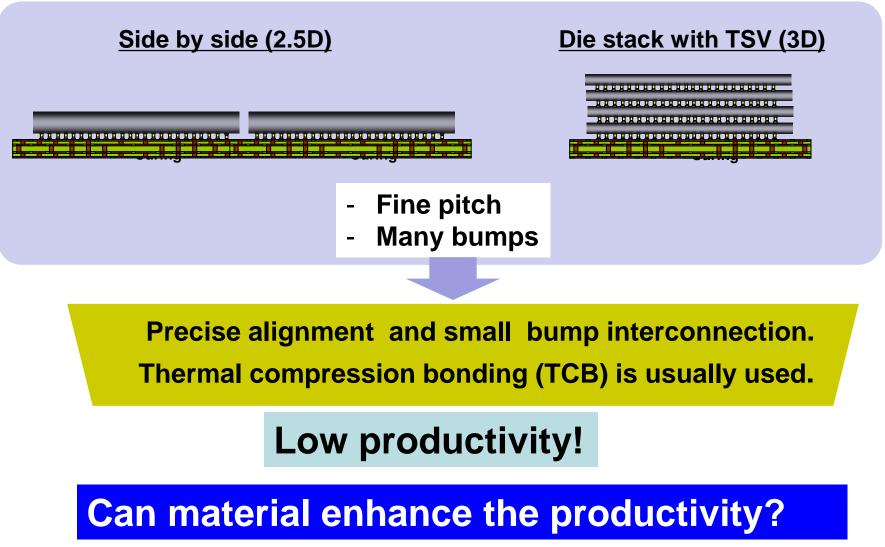


## **Can material do other contributions?**

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### **Issues of high density interconnecting**

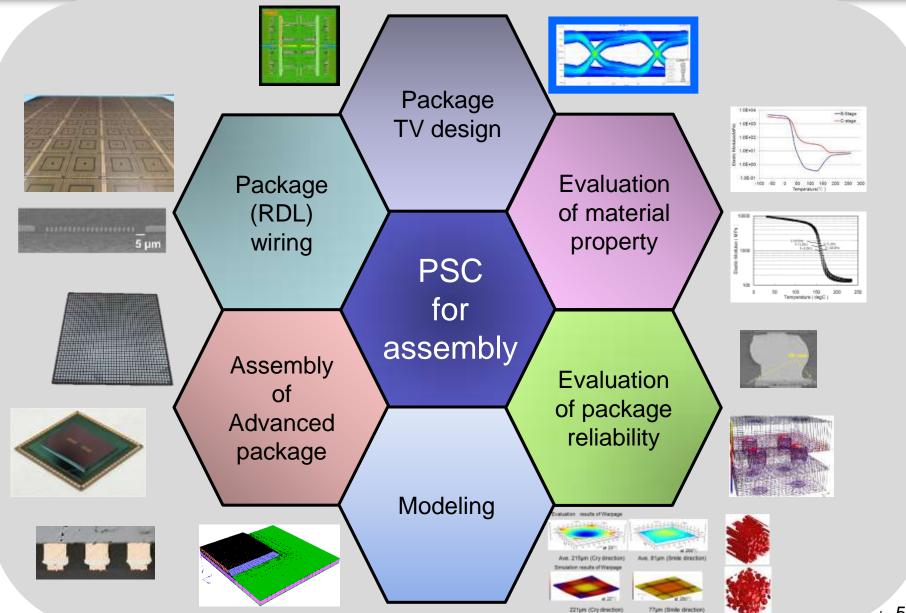
#### Typical die configurations of high density packages



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Working On Wonders

#### Function of Packaging Solution Center (PSC) of HC



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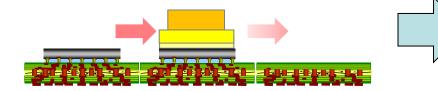
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# Contents

- **1. Materials for high density packaging**
- 2. Bonding Force Leveling (BFL) Film
- 3. Molded reflow process with NCF & EMC
- 4. Bump Stabbing process
- 5. RDL-first FO-PLP TV and "JOINT"
- 6. Summary

#### Conventional TCB process

**Pre-bonding** 



Main bonding (die by die)

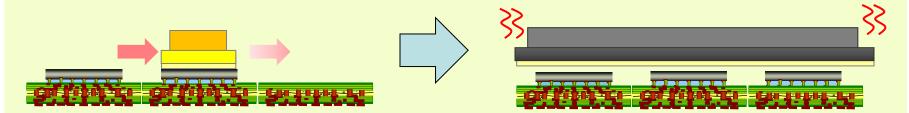
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The die by die sequential process step

#### Gang-bonding process

**Pre-bonding** 

#### Main bonding (gang-bonding)



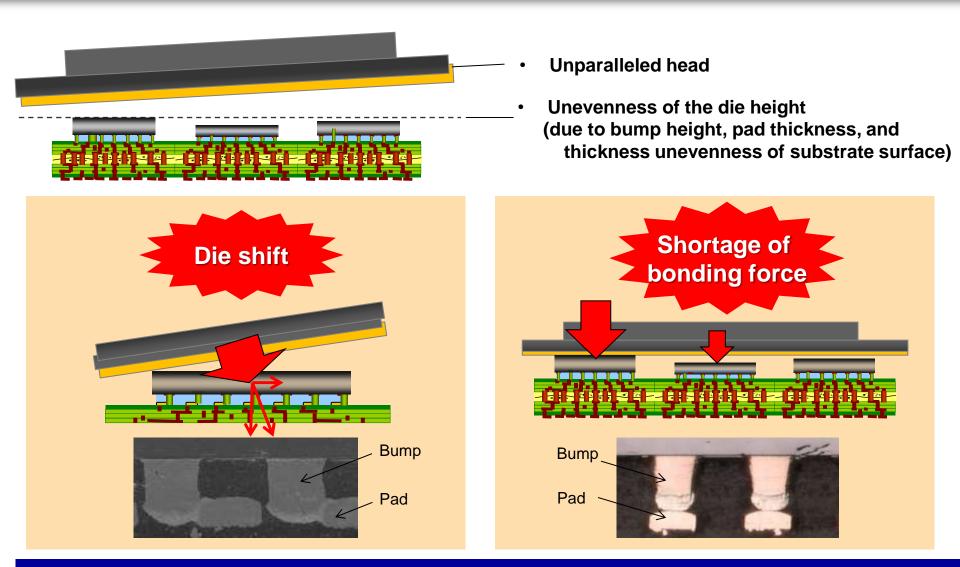
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Multi die soldering on the substrate with single large head

Gang-bonding process can significantly enhance the productivity

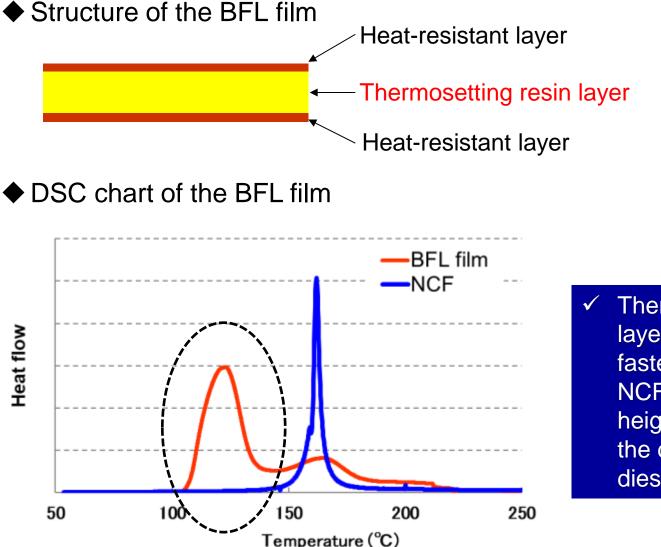
#### **Issues of gang bonding on TCB**





Die shift and the shortage of bonding force may happen at the gang-bonding

## **Characteristics of the BFL film**



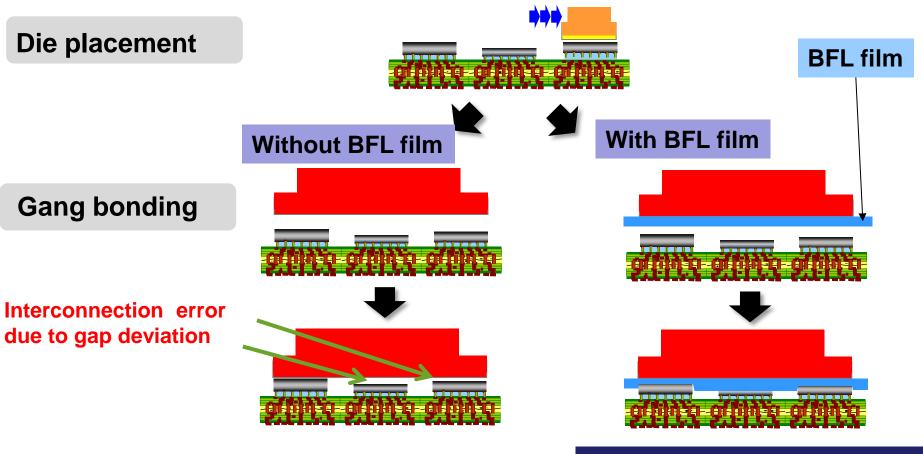
 Thermosetting resin layer of BFL film cures faster than the resin of NCF to compensate the height difference among the dies before multi dies gang bonding.

**BFL: Bonding Force Leveling** 

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## **BFL film compensates the deviation**

**BFL** can enhance the productivity of TCB process



BFL can compensate the gap deviation High productivity gang bonding !

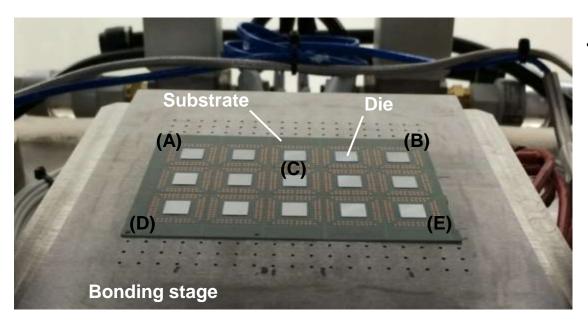
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#### Set up of the test of CoS gang-bonding with BFL

#### Test vehicle specification

Die	7.3 mm × 7.3 mm, 100 µm <sup>t</sup>	
	Peripheral bump : 80µm pitch	<b>100</b>
	Full array bump : 300µm pitch	
	Bump height : Cu Pillar (30 µm <sup>t</sup> )	
	+SnAg Solder (15 µm <sup>t</sup> )	
Substrate	Top layer Cu thickness: 15 µm	
	Total thickness: 0.36 mm	TV appearance
NCF	Thickness: 40 µm	



- Condition: 80 °C/50 N/3 s
- Gang bonding by HTB-MM (Alpha Design Co., Ltd.) Condition: 300 °C/750 N/15 s

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#### Evaluation

- Daisy chain (all dies)
- Die shift (A-E dies)
- Void in NCF

#### The results of gang-bonding with BFL

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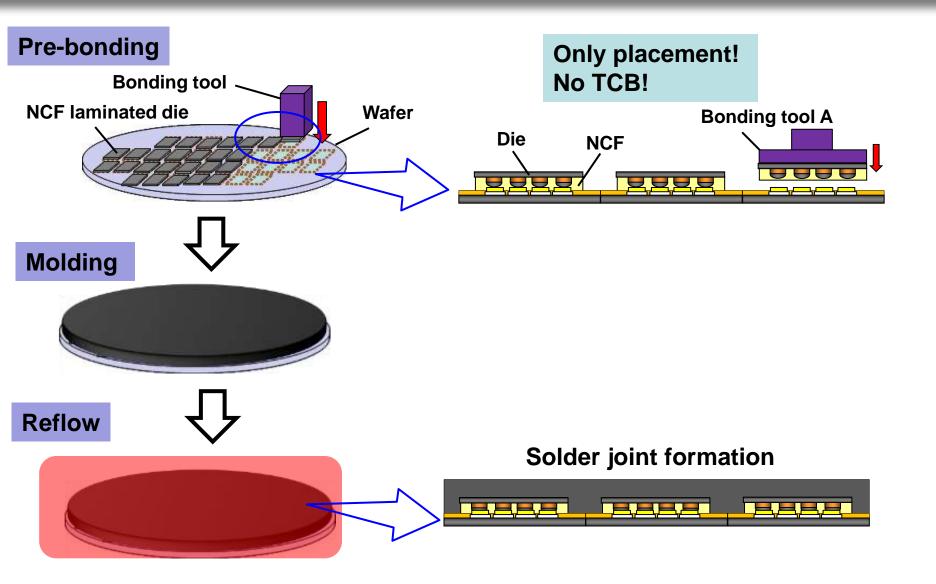
Item	No film	Teflon	BFL film
Daisy chain test ( Pass /Total )	8/15	14/15	15/15
Die shift after pre-bonding	80 60 60 20 20 (C) (B) (B) (B) (C) (D) (C) (D) (A) (E) (A) -20 -80 -80 -80 -80 -80 -80 -80 -8	(un) 20 40 20 50 40 (E) (B) (D) (C) (A) 40 (C) (A) 40 (C) (A) 40 40 (C) (C) 40 (C) (A) 40 40 40 40 40 40 40 40 40 40	80      90      60      40      51      20      60
Ave. die shift	30 µm	27 µm	5 µm
Void in NCF by C-SAM observation			
	NG	OK	OK

The BFL film performed worked well at 15-die gang bonding

# Contents

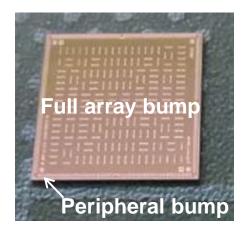
- Materials for high density packaging
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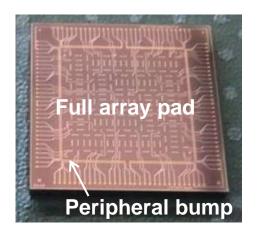
### "Molded reflow " process



## **Die specification of TV**

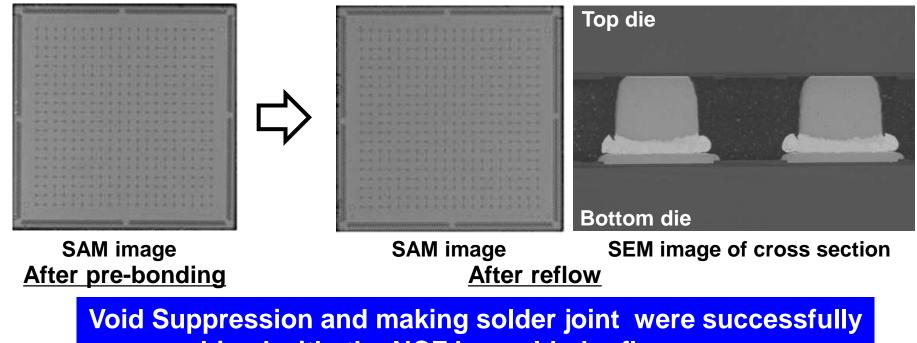
	7.3 mm x 7.3 mm, 100 μm <sup>t</sup>
	Passivation : SiN
Top dia	Peripheral bump : 80 µm pitch, 648 pin
Top die	Full array bump : 300 µm pitch, 400 pin
	Bump height :
	Cu Pillar (30 µm <sup>t</sup> ) + Sn/Ag Solder (15 µm <sup>t</sup> )
	10 mm×10 mm, 100 μm <sup>t</sup>
Bottom die	Passivation : SiN
	Pad : Ni/Au plating





## **CoC** assembly by molded reflow

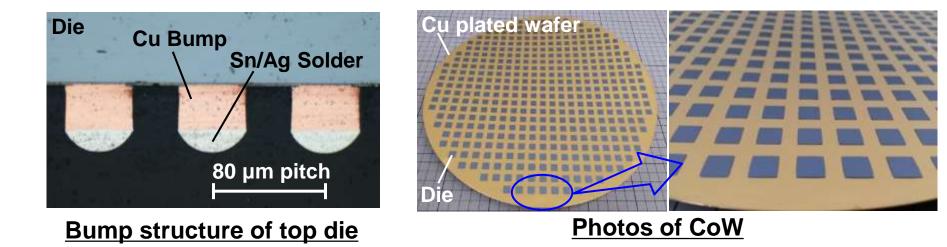
NCF: Specially designed for reflow process (Lower viscosity NCF). Pre-bonding condition: 130°C/2 s Reflow condition: 170°C/2 min + 190°C/2 min + 260°C/2 min + 190°C/2 min by convection ovens.



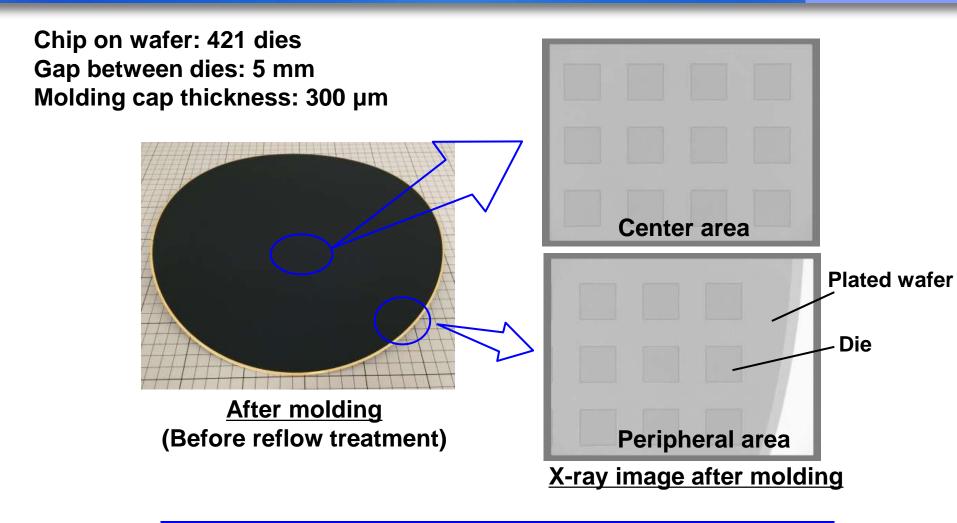
archived with the NCF by molded reflow process.

### **CoW assembly by molded reflow**

Top die	Size : 7.3 mm × 7.3 mm , Thickness 100 μm	
	Peripheral bump : 80 µm pitch, 328 pin	
	Bump height :	
	Cu Pillar (30 μm) + Sn/Ag Solder (15 μm)	
	12 inch wafer , Thickness 250 µm	
Plated wafer	Plating thickness :	
Walci	Cu 4 μm/ Ni 4 μm /Au 0.1 μm	

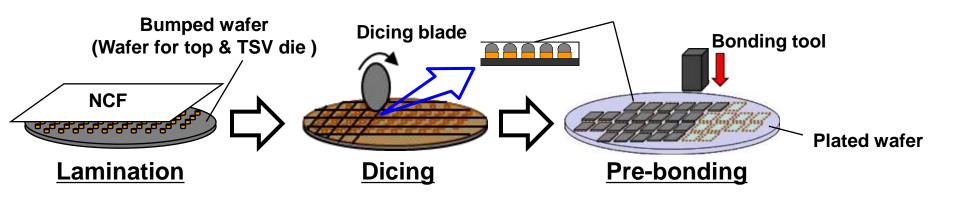


## X-ray image of molded reflow CoW



No die shift was observed.

### 3D die stacking TSV-PKG assembly by Molded reflow process





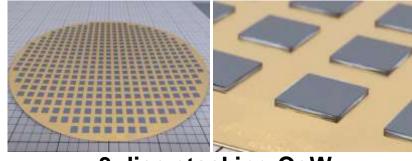
<u>3 die stacking</u> (Under pre-bonding condition)



**Reflow treatment** 

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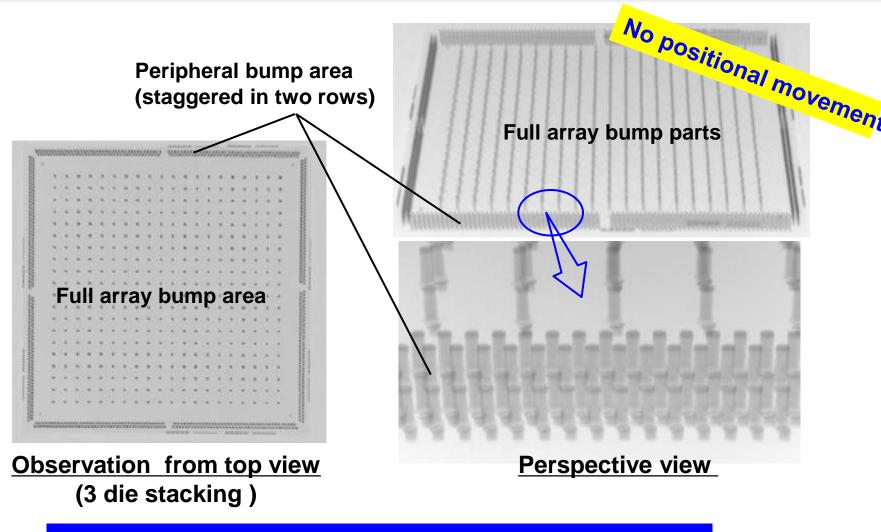
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Chip on wafer:  $421 \times 3 = 1263$  dies Gap between dies: 5 mm

3 dies stacking CoW

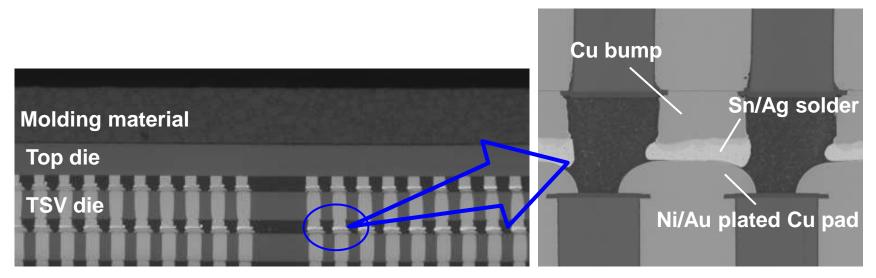
## X-ray image after over-molding



No die shift was observed by over-molding.

## **Cross section of TSV-3D die stacking**

Molding cap thickness: 500 µm



Cross section after reflow

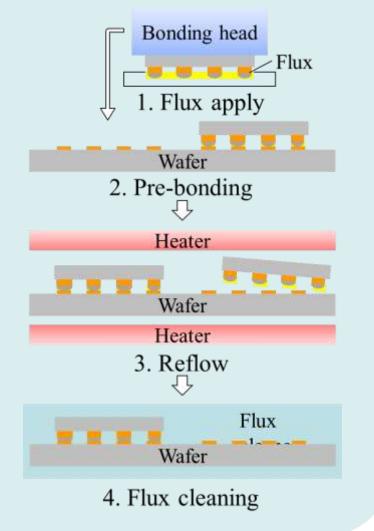
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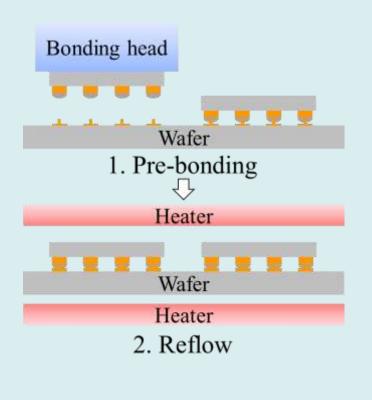
### **Bump stabbing assembly**



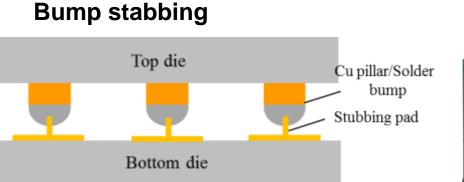




#### Bump stabbing mass reflow process



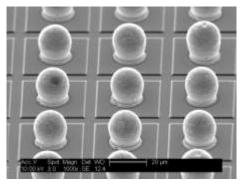
### **Test vehicle specification**



#### Top die



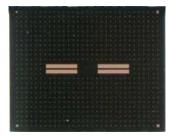
#### Bumps of the top die



#### **TV die specifications**

Top die	Size	10 x 8 mm
	Thickness	0.725 mm
	Bump pitch	I/O : 40 μm Dummy : 300 μm
	Bump size	Φ20 μm
	Bump height	Cu/Sn-Ag : 10 μm/8 μm
	Size	10 x 8 mm
Bottom die	Thickness	0.725 mm
	Pad pitch	I/O : 40 μm Dummy : 300 μm
	Pad size	Ф26 µm
	Pad height	Bottom/Stubbing 2 μm/3 μm

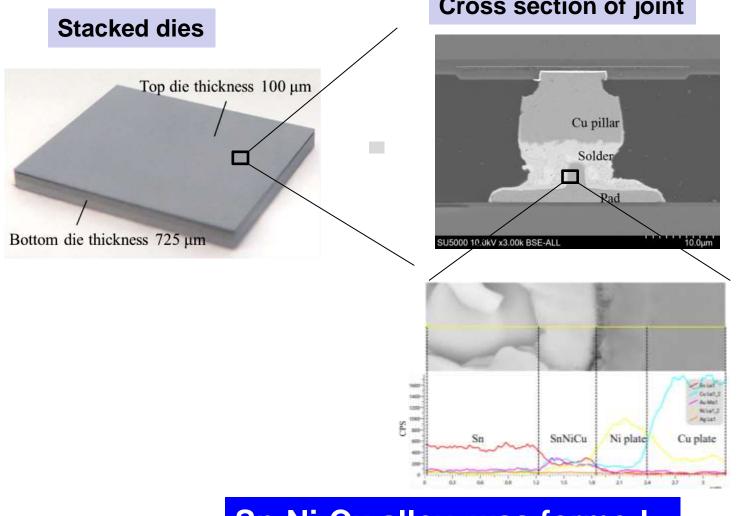
#### **Bottom die**



#### Pads of the bottom die



### Solder joint by bump stabbing



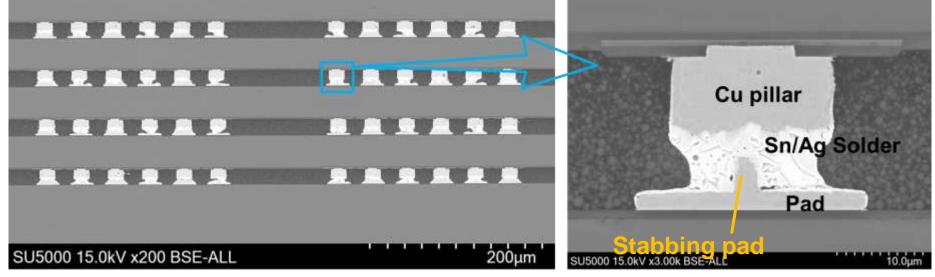
#### **Cross section of joint**

### Sn-Ni-Cu alloy was formed.

## **3D die stacking**



Die thickness : 40 µm Stack layer : 4



#### Cross section after reflow treatment

Solder joints were formed with good alignment

\*Details will be presented at session 33-4 (3:30 pm on June 1)

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### **Consortium "JOINT" has been founded!**

State of the art jisso technologies of material and equipment get together, which can provide the solution.



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Enhancement of the productivity of high density interconnection was studied and demonstrated, which were related 2.5D and 3D packages.

- BFL film : Side by side multiple die TCB gang bonding
- Molded reflow: CoW multiple die bonding including 3D die stacking
- Bump stabbing process: 3D die stacking
- Expanding film
- RDL first FO
- Consortium "JOINT"

# Thank you!

# Hitachi Chemical Working On Wonders

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